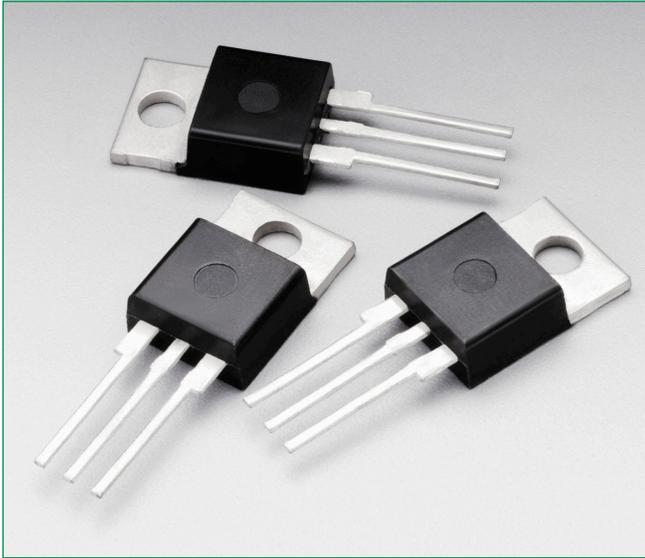


MAC15M, MAC15N



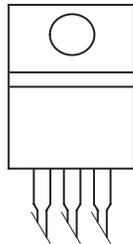
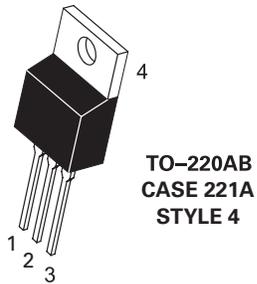
Description

Designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

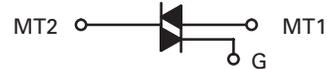
Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt – 250 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO–220 Package
- High Commutating di/dt – 9.0 A/ms minimum at 125°C
- Operational in Three Quadrants, Q1, Q2, and Q3

Pin Out



Functional Diagram



Additional Information



[Datasheet](#)



[Resources](#)



[Samples](#)

Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (– 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V_{DRM} V_{RRM}	600 800	V
MAC15A6G			
MAC15–8G, MAC15A8G			
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, $T_C = 80^\circ\text{C}$)	$I_{\text{T (RMS)}}$	15	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_J = 125^\circ\text{C}$) Preceded and Followed by Rated Current	I_{TSM}	150	A
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	93	A ² sec
Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = 1.0 μs)	P_{GM}	20	W
Average Gate Power ($t = 8.3$ ms, $T_C = 80^\circ\text{C}$)	$P_{\text{G (AV)}}$	0.5	W
Operating Junction Temperature Range	T_J	–40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	–40 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC)	R_{8JC}	2.0	$^\circ\text{C/W}$
Junction-to-Ambient	R_{8JA}	62.5	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Electrical Characteristics - OFF ($T_J = 25^\circ\text{C}$ unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Repetitive Blocking Current ($V_D = V_{DRM} = V_{RRM}$; Gate Open)	$T_J = 25^\circ\text{C}$	I_{DRM}	-	-	0.01	μA
	$T_J = 125^\circ\text{C}$	I_{RRM}	-	-	2.0	mA

Electrical Characteristics - ON ($T_J = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak On-State Voltage (Note 2) ($I_{TM} = \pm 21$ A Peak)		V_{TM}	-	1.2	1.6	V
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 100$ Ω)	MT2(+), G(+)	I_{GT}	5.0	13	35	mA
	MT2(+), G(-)		5.0	16	35	
	MT2(-), G(-)		5.0	18	35	
Gate Trigger Voltage (Continuous dc) ($V_D = 12$ V, $R_L = 100$ Ω)	MT2(+), G(+)	V_{GT}	0.5	0.75	1.5	V
	MT2(+), G(-)		0.5	0.72	1.5	
	MT2(-), G(-)		0.5	0.82	1.5	
Latching Current ($V_D = 24$ V, $I_G = 35$ mA)	MT2(+), G(+)	V_{GD}	-	33	50	V
	MT2(+), G(-)		-	36	80	
	MT2(-), G(-)		-	33	50	
Holding Current ($V_D = 12$ V _{dc} , Gate Open, Initiating Current = ± 200 mA)		I_H	-	20	40	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

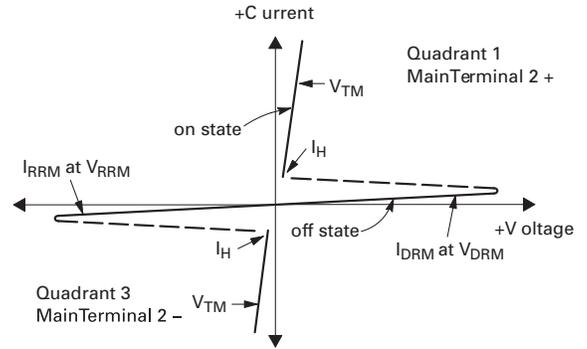
2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle $\leq 2\%$.

Dynamic Characteristics

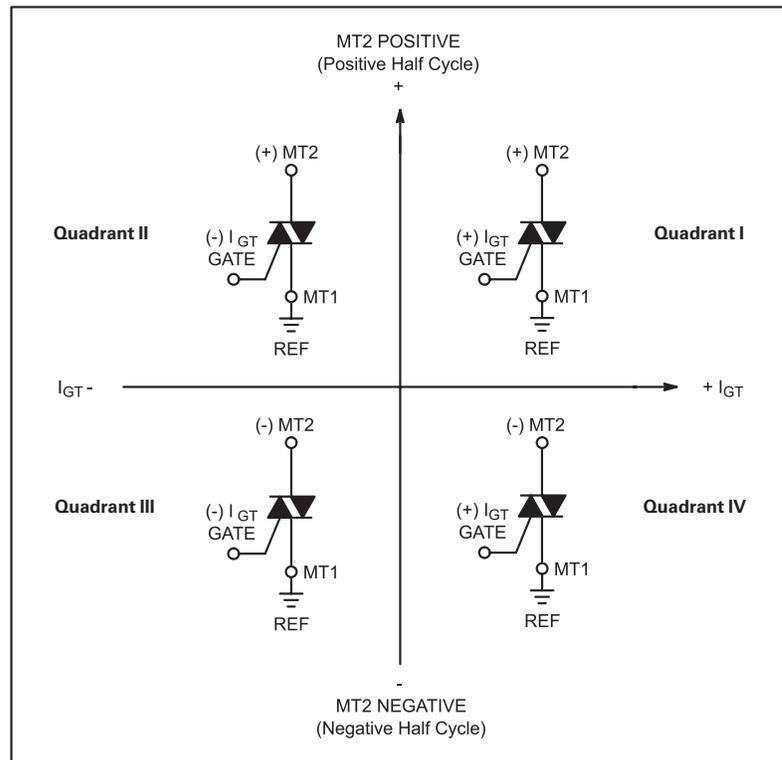
Characteristic		Symbol	Min	Typ	Max	Unit
Rate of Change of Commutating Current; See Figure 10. ($V_D = 400$ V, $I_{TM} = 6.0$ A, Commutating $dv/dt = 24$ V/ μs , Open, $T_J = 125^\circ\text{C}$, $f = 250$ Hz, No Snubber)	$C_L = 10$ μF Gate $L_L = 40$ mH	$(di/dt)_c$	9.0	-	-	A/ms
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^\circ\text{C}$)		dv/dt	250	-	-	V/ μs

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

Figure 1. RMS Current Derating

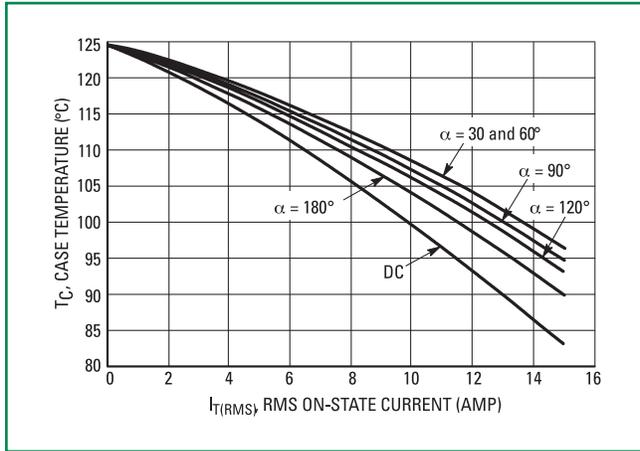


Figure 2. On-State Power Dissipation

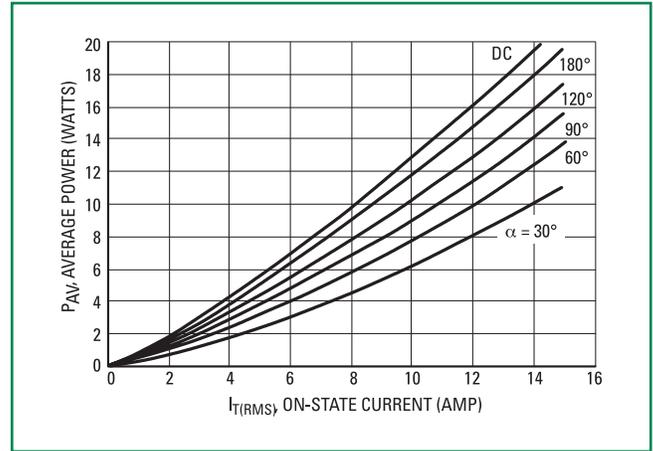


Figure 5. On-State Characteristics

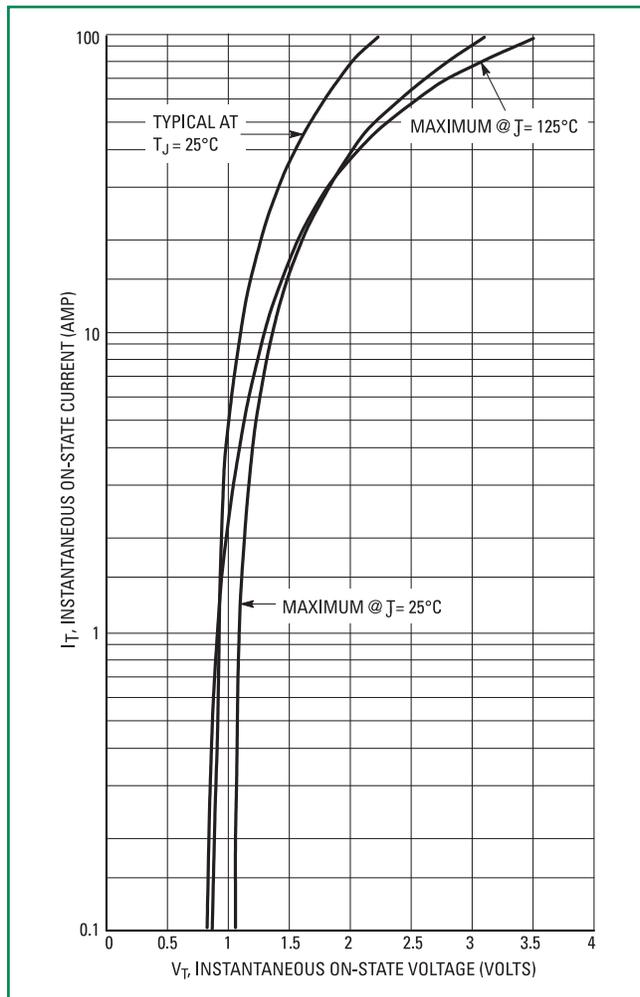


Figure 4. Transient Thermal Response

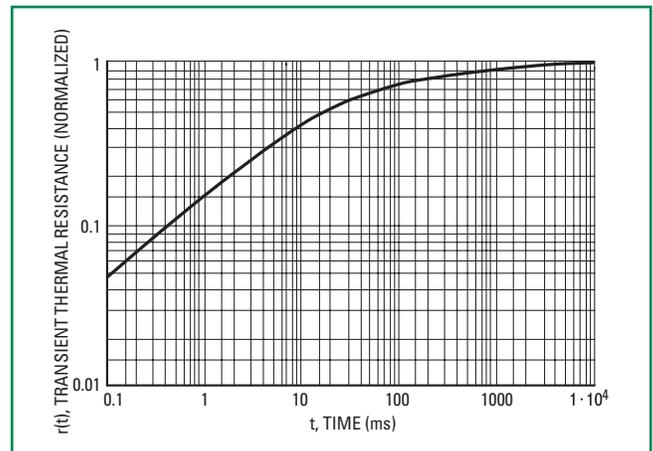


Figure 5. Hold Current Variation

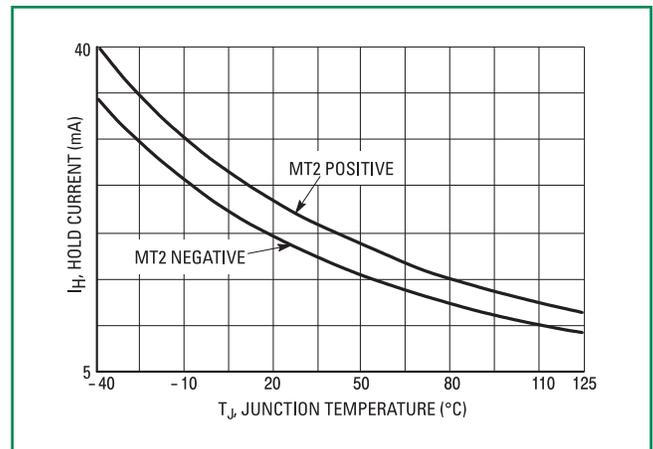


Figure 6. Typical Holding Current vs Junction Temperature

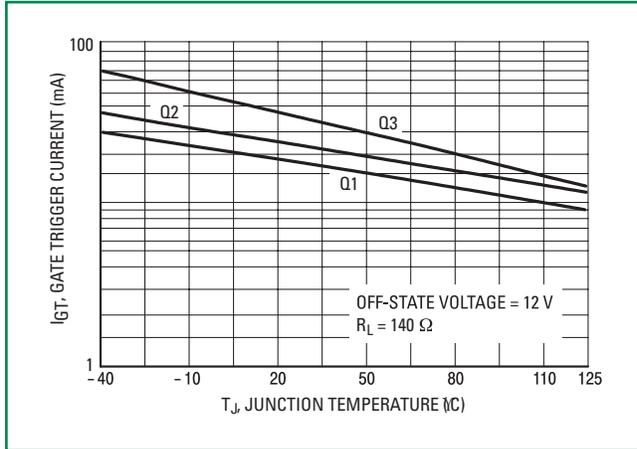


Figure 7. Gate Trigger Voltage vs Junction Temperature

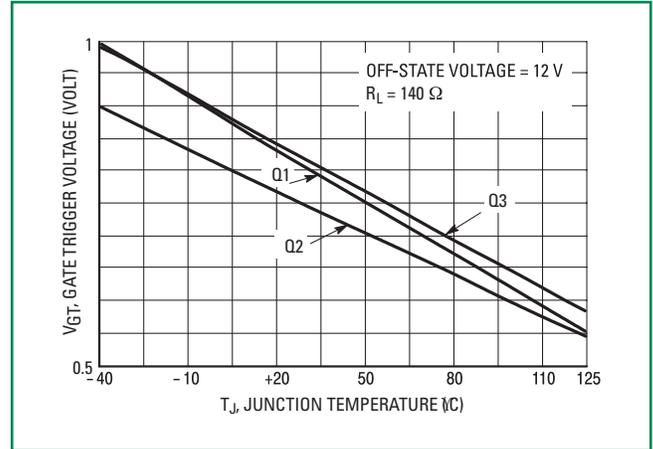


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential)

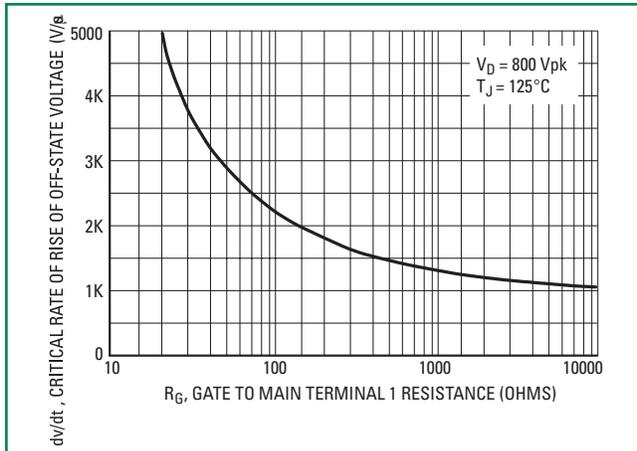


Figure 9. Critical Rate of Rise of Commutating Voltage

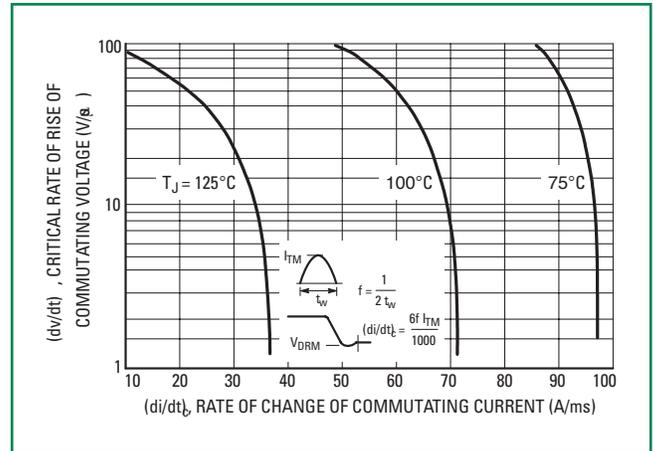
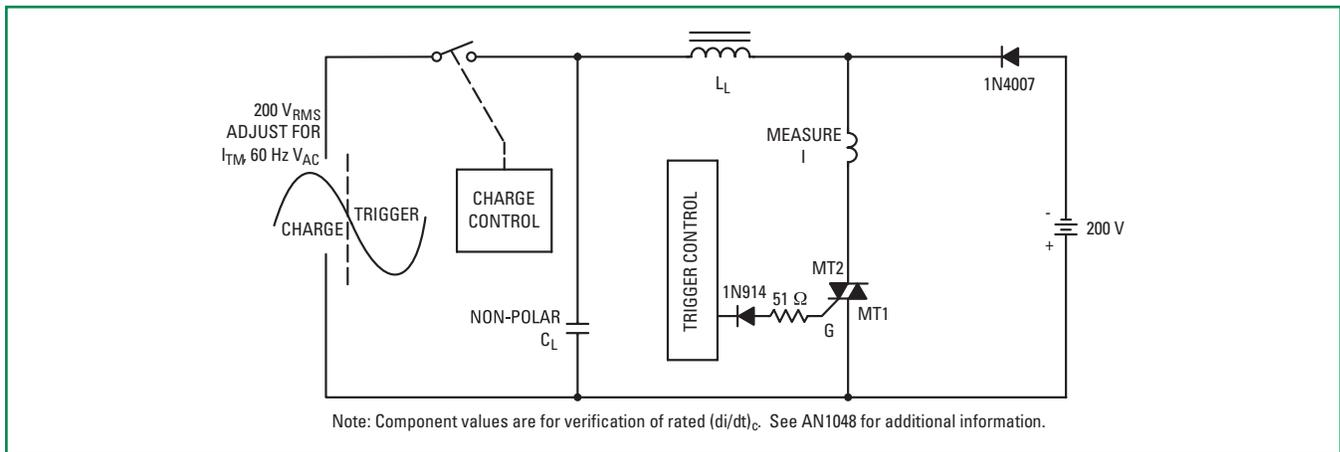
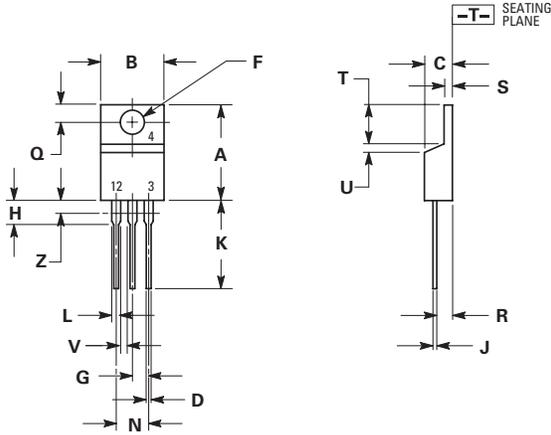


Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c



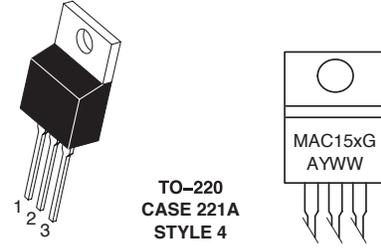
Dimensions



Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Part Marking System



- TO-220
CASE 221A
STYLE 4
- x= M or N
 - A= Assembly Location
 - Y= Year
 - WW = Work Week
 - G = Pb-Free Package

Pin Assignment

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

Ordering Information

Device	Package	Shipping
MAC15MG	TO-220 (Pb-Free)	50 Units/ Rail
MAC15NG		

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